TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC4066AP,TC74HC4066AF,TC74HC4066AFN,TC74HC4066AFT

Quad Bilateral Switch

The TC74HC4066A is a high speed CMOS QUAD BILATERAL SWITCH fabricated with silicon gate C^2MOS technology.

It consists of four independent high speed switches capable of controlling either digital or analog signals while maintaining the CMOS low power dissipation.

Control input (C) is provided to control the switch. The switch turns ON while the C input is high, and the switch turns OFF while low.

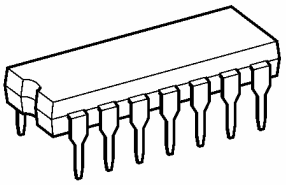
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

- High speed: t_{pd} = 7 ns (typ.) at V_{CC} = 5 V
- Low power dissipation: I_{CC} = 1 μA (max) at Ta = 25°C
- High noise immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC} (min)
- Low on resistance: R_{ON} = 50 Ω (typ.) at V_{CC} = 9 V
- High degree of linearity: THD = 0.05% (typ.) at V_{CC} = 5 V
- Pin and function compatible with 4066B

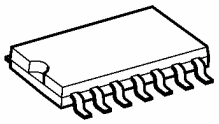
Note: xxxFN (JEDEC SOP) is not available in Japan.

TC74HC4066AP

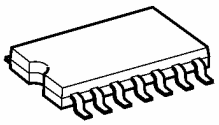


DIP14-P-300-2.54

TC74HC4066AF

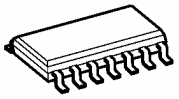


SOP14-P-300-1.27A



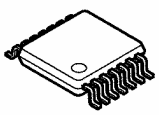
SOP14-P-300-1.27

TC74HC4066AFN



SOL14-P-150-1.27

TC74HC4066AFT

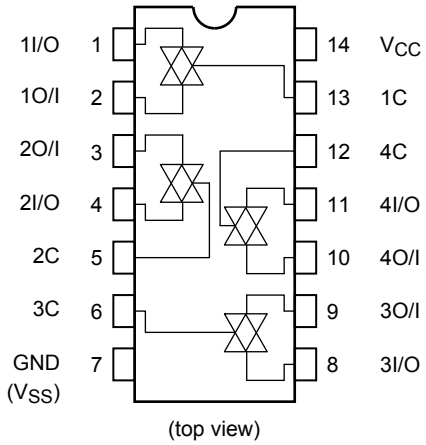


TSSOP14-P-0044-0.65A

Weight

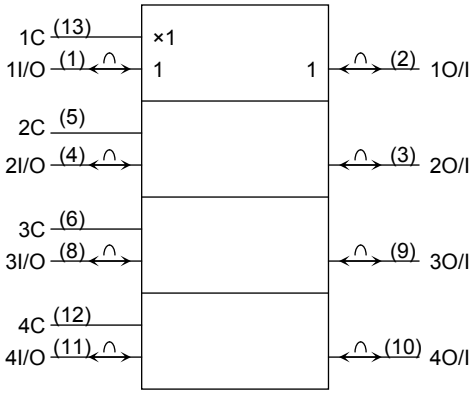
DIP14-P-300-2.54	: 0.96 g (typ.)
SOP14-P-300-1.27A	: 0.18 g (typ.)
SOP14-P-300-1.27	: 0.18 g (typ.)
SOL14-P-150-1.27	: 0.12 g (typ.)
TSSOP14-P-0044-0.65A	: 0.06 g (typ.)

Pin Assignment



(top view)

IEC Logic Symbol



Truth Table

Control	Switch Function
H	On
L	Off

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	−0.5 to 13	V
Control input voltage	V_{IN}	−0.5 to V_{CC} + 0.5	V
Switch I/O voltage	$V_{I/O}$	−0.5 to V_{CC} + 0.5	V
Control input diode current	I_{IK}	±20	mA
I/O diode current	I_{OK}	±20	mA
Switch through Current	I_{OUT}	±25	mA
DC V_{CC}/ground current	I_{CC}	±50	mA
Power dissipation	P_D	500 (DIP) (Note 2)/180 (SOP/TSSOP)	mW
Storage temperature	T_{stg}	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: 500 mW in the range of Ta = −40 to 65°C. From Ta = 65 to 85°C a derating factor of −10 mW/°C should be applied up to 300 mW.

Recommended Operating Conditions (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	2 to 12	V
Control input voltage	V_{IN}	0 to V_{CC}	V
Switch I/O voltage	$V_{I/O}$	0 to V_{CC}	V
Operating temperature	T_{opr}	−40 to 85	°C
Input rise and fall time	t_r, t_f	0 to 1000 (V_{CC} = 2.0 V) 0 to 500 (V_{CC} = 4.5 V) 0 to 400 (V_{CC} = 6.0 V) 0 to 250 (V_{CC} = 10.0 V)	ns

Note: The recommended operating conditions are required to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = −40 to 85°C		Unit
			V_{CC} (V)	Min	Typ.	Max	Min	Max	
High-level control input voltage	V_{IHC}	—	2.0	1.50	—	—	1.50	—	V
			4.5	3.15	—	—	3.15	—	
			9.0	6.30	—	—	6.30	—	
			12.0	8.40	—	—	8.40	—	
Low-level control input voltage	V_{ILC}	—	2.0	—	—	0.50	—	0.50	V
			4.5	—	—	1.35	—	1.35	
			9.0	—	—	2.70	—	2.70	
			12.0	—	—	3.60	—	3.60	
On resistance	R_{ON}	$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ to GND $I_{I/O} \leq 1$ mA	4.5	—	96	170	—	200	Ω
			9.0	—	55	85	—	100	
			12.0	—	45	80	—	90	
		$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ or GND $I_{I/O} \leq 1$ mA	2.0	—	160	—	—	—	
			4.5	—	70	100	—	130	
			9.0	—	50	75	—	95	
			12.0	—	45	70	—	90	
Difference of on resistance between switches	ΔR_{ON}	$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ to GND $I_{I/O} \leq 1$ mA	4.5	—	10	—	—	—	Ω
			9.0	—	5	—	—	—	
			12.0	—	5	—	—	—	
Input/output leakage current (switch off)	I_{OFF}	$V_{OS} = V_{CC}$ or GND V_{IS} = GND or V_{CC} $V_{IN} = V_{ILC}$	12.0	—	—	±100	—	±1000	nA
Switch input leakage current (switch on, output open)	I_{IZ}	$V_{OS}=V_{CC}$ or GND $V_{IN} = V_{IHC}$	12.0	—	—	±100	—	±1000	nA
Control input current	I_{IN}	$V_{IN} = V_{CC}$ or GND	12.0	—	—	±100	—	±1000	nA
Quiescent supply current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	1.0	—	10.0	μA
			9.0	—	—	4.0	—	40.0	
			12.0	—	—	8.0	—	80.0	

AC Characteristics (C_L = 50 pF, input: $t_r = t_f$ = 6 ns)

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = −40 to 85°C		Unit
			VCC (V)	Min	Typ.	Max	Min	Max	
Phase difference between input and output	φ_{I-O}	—	2.0	—	10	50	—	65	pF
			4.5	—	4	10	—	13	
			9.0	—	3	8	—	10	
			12.0	—	3	7	—	9	
Output enable time	t_{pZL} t_{pZH}	R_L = 1 kΩ	2.0	—	18	100	—	125	pF
			4.5	—	8	20	—	25	
			9.0	—	6	12	—	22	
			12.0	—	6	12	—	18	
Output disable time	t_{pLZ} t_{pHZ}	R_L = 1 kΩ	2.0	—	20	115	—	145	pF
			4.5	—	10	23	—	29	
			9.0	—	8	20	—	25	
			12.0	—	8	18	—	22	
Maximum control input frequency		R_L = 1 kΩ C_L = 15 pF V_{OUT} = 1/2 V_{CC}	2.0	—	30	—	—	—	MHz
			4.5	—	30	—	—	—	
			9.0	—	30	—	—	—	
			12.0	—	30	—	—	—	
Control input capacitance	C_{IN}	—		—	5	10	—	10	pF
Switch terminal capacitance	$C_{I/O}$	—		—	6	—	—	—	pF
Feed through capacitance	C_{IOS}	—		—	0.5	—	—	—	pF
Power dissipation capacitance	C_{PD}	(Note)		—	15	—	—	—	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per channel)}$$

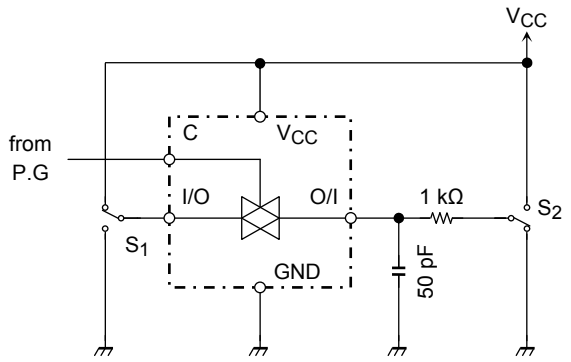
Analog Switch Characteristics (GND = 0 V, Ta = 25°C) (Note)

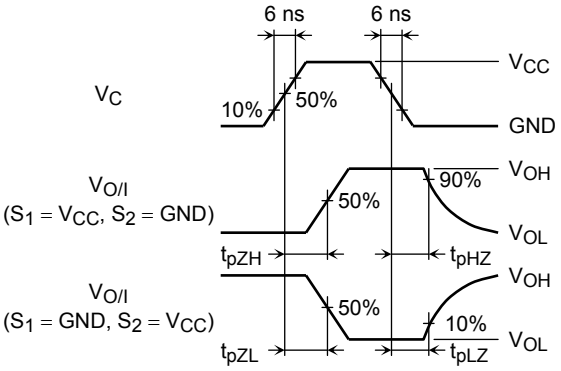
Characteristics	Symbol	Test Condition	V_{CC} (V)	Typ.	Unit
Sine wave distortion (T.H.D)		f_{IN} = 1 kHz, V_{IN} = 4 V_{p-p}, @V_{CC} = 4.5 V R_L = 10 kΩ, V_{IN} = 8 V_{p-p}, @V_{CC} = 9.0 V C_L = 50 pF	4.5 9.0	0.05 0.04	%
Frequency response (switch on)	f_{max}	Adjust f_{IN} voltage to obtain 0dBm at V_{OS} Increase f_{IN} frequency until dB meter reads −3dB R_L = 50 Ω, C_L = 10 pF f_{IN} = 1 MHz, sine wave	4.5 9.0	200 200	MHz
Feedthrough attenuation (switch off)		Vin is centered at V_{CC}/2 Adjust input for 0dBm R_L = 600 Ω, C_L = 50 pF f_{IN} = 1 MHz, sine wave	4.5 9.0	−60 −60	dB
Crosstalk (control input to signal output)		R_L = 600 Ω, C_L = 50 pF f_{IN} = 1 MHz, square wave (t_r = t_f = 6 ns)	4.5 9.0	60 100	mV
Crosstalk (between any switches)		Adjust V_{IN} to obtain 0dBm at input R_L = 600 Ω, C_L = 50 pF f_{IN} = 1 MHz, sine wave	4.5 9.0	−60 −60	dB

Note: These characteristics are determined by design of devices.

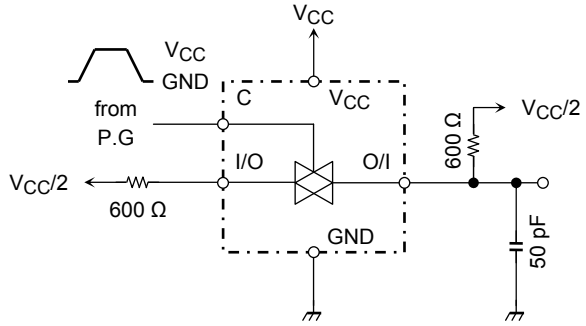
Switching Characteristics Test Circuits

1. t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}

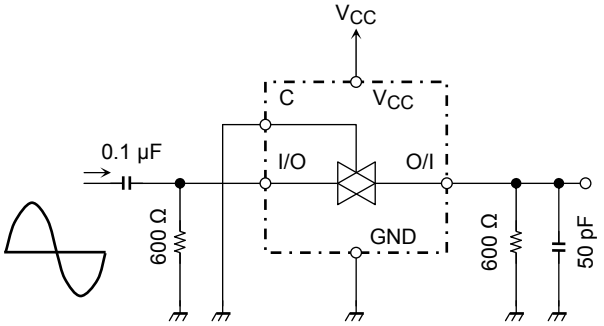




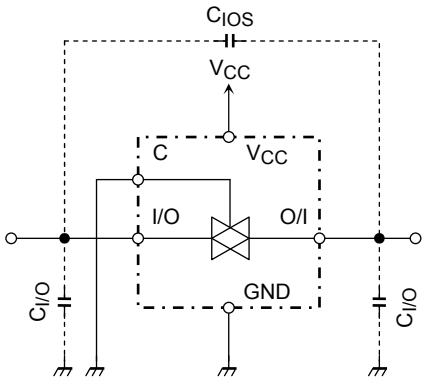
2. Cross Talk (control input-switch output) fIN = 1 MHz duty = 50% tr = tf = 6 ns



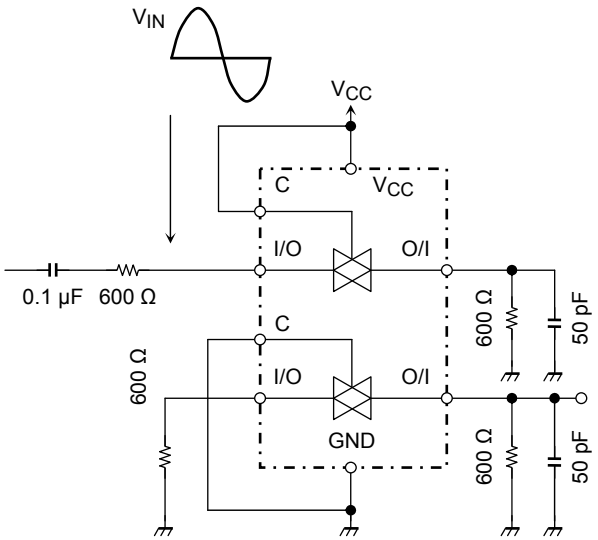
3. Feedthrough Attenuation



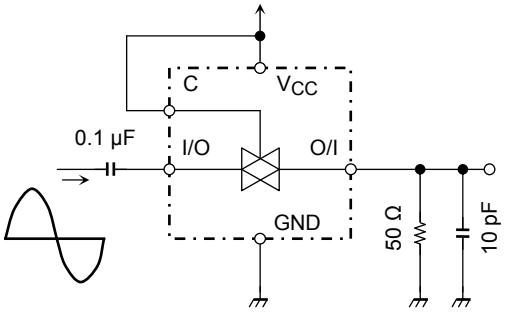
4. C_{IOS}, $C_{I/O}$



5. Crosstalk (between any two switches)

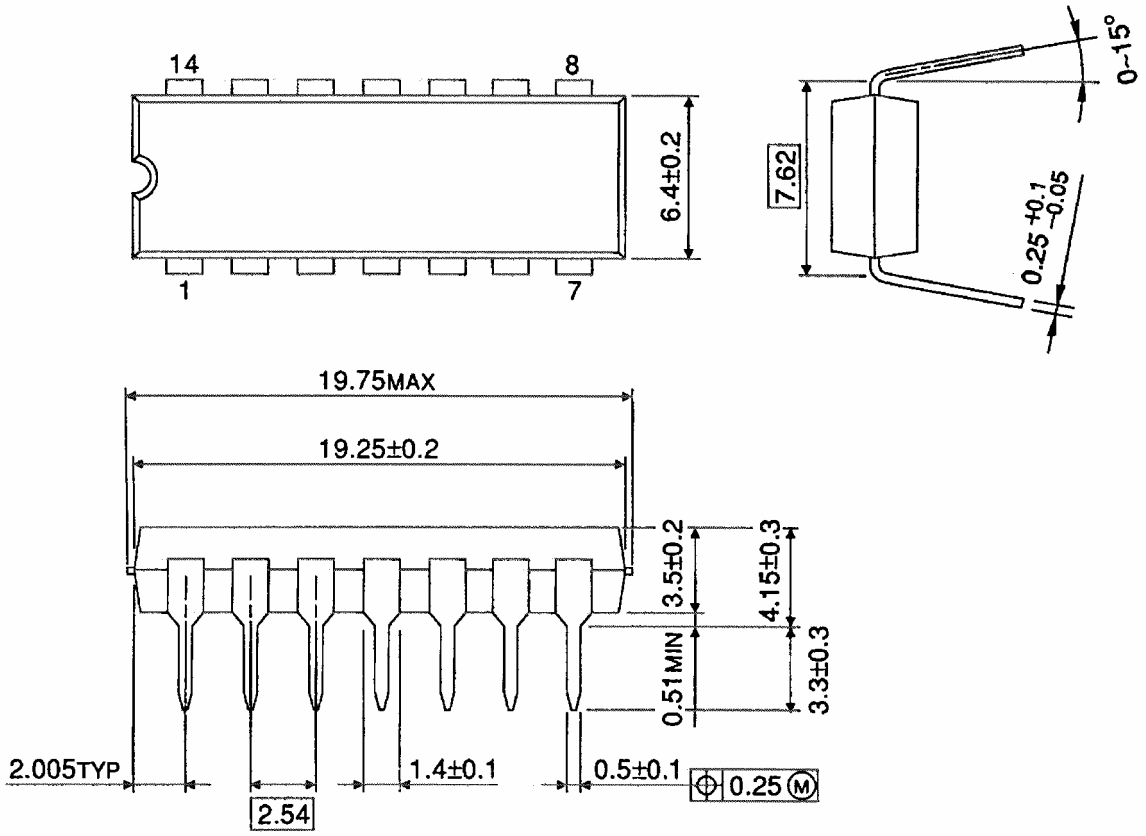


6. Frequency Response (switch on)



Package Dimensions

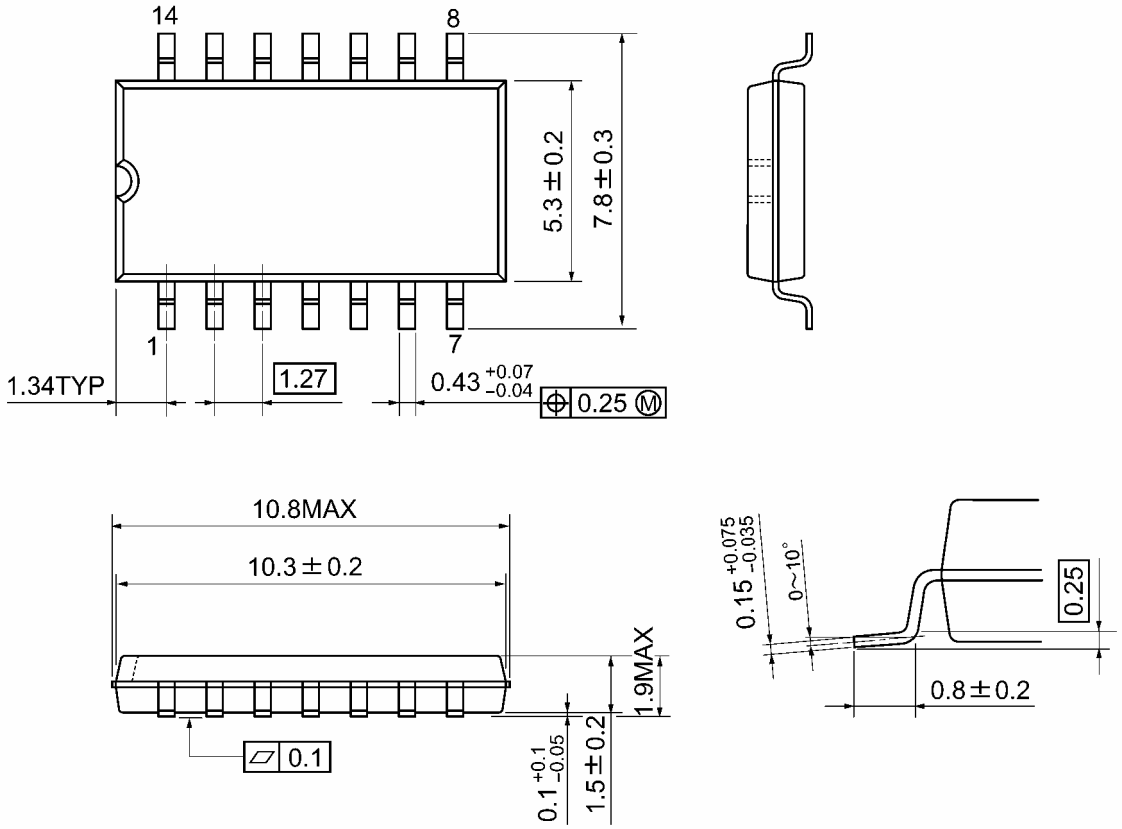
DIP14-P-300-2.54 Unit : mm



Weight: 0.96 g (typ.)

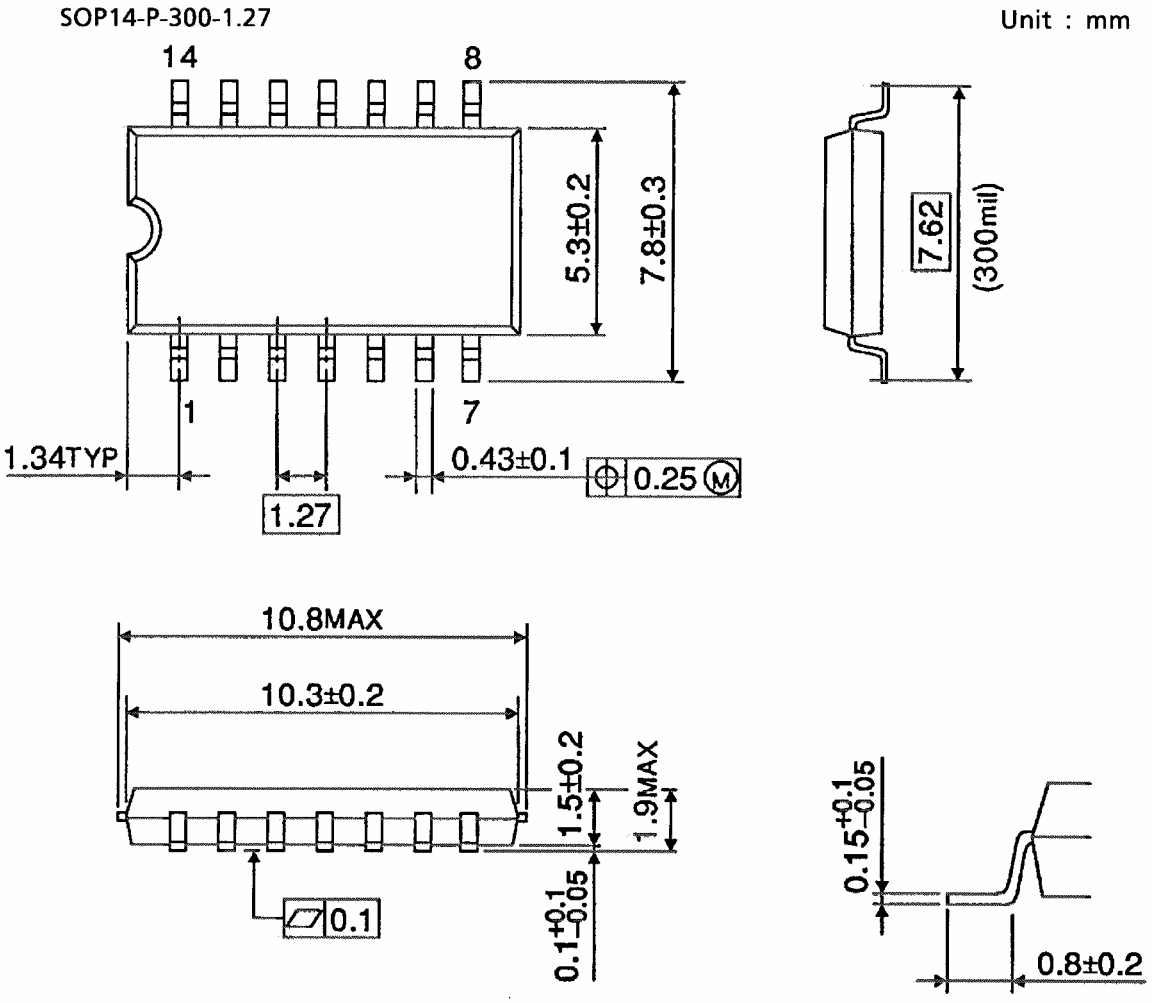
Package Dimensions

SOP14-P-300-1.27A Unit: mm



Weight: 0.18 g (typ.)

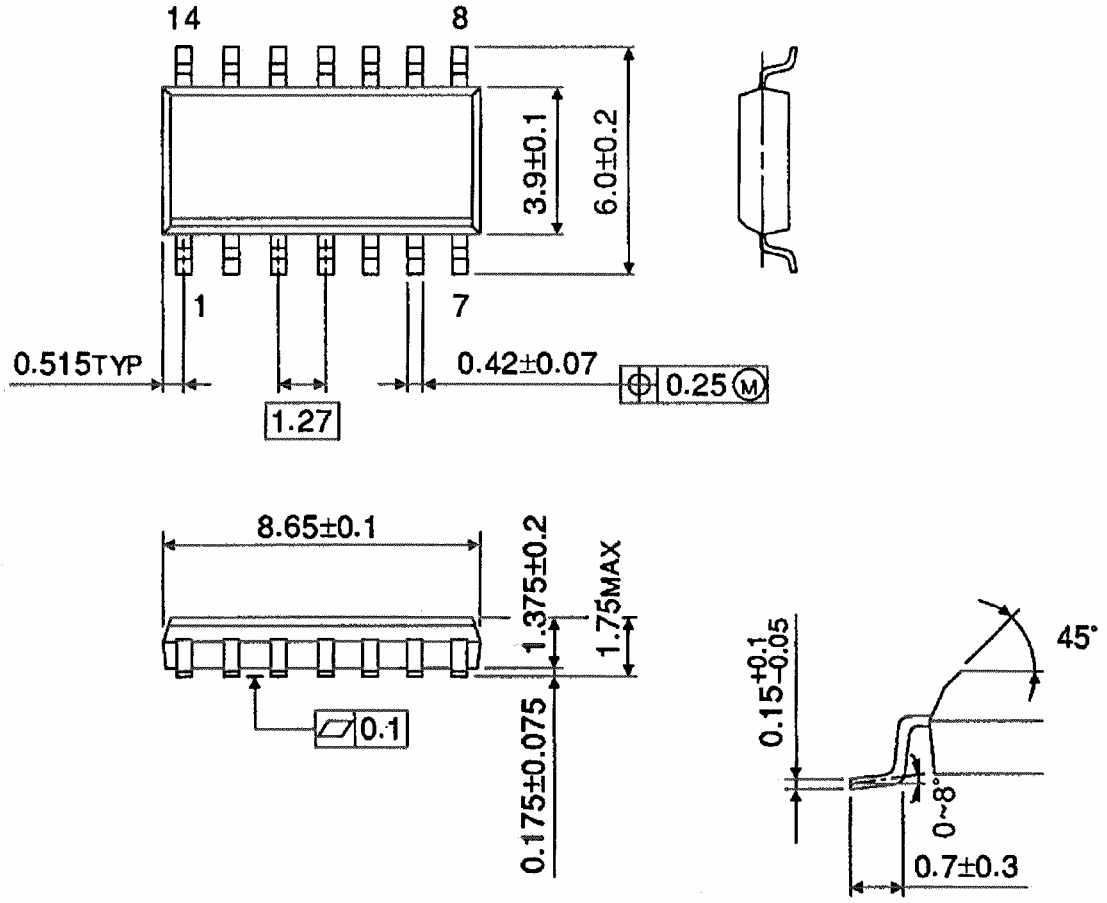
Package Dimensions



Weight: 0.18 g (typ.)

Package Dimensions (Note)

SOL14-P-150-1.27 Unit : mm

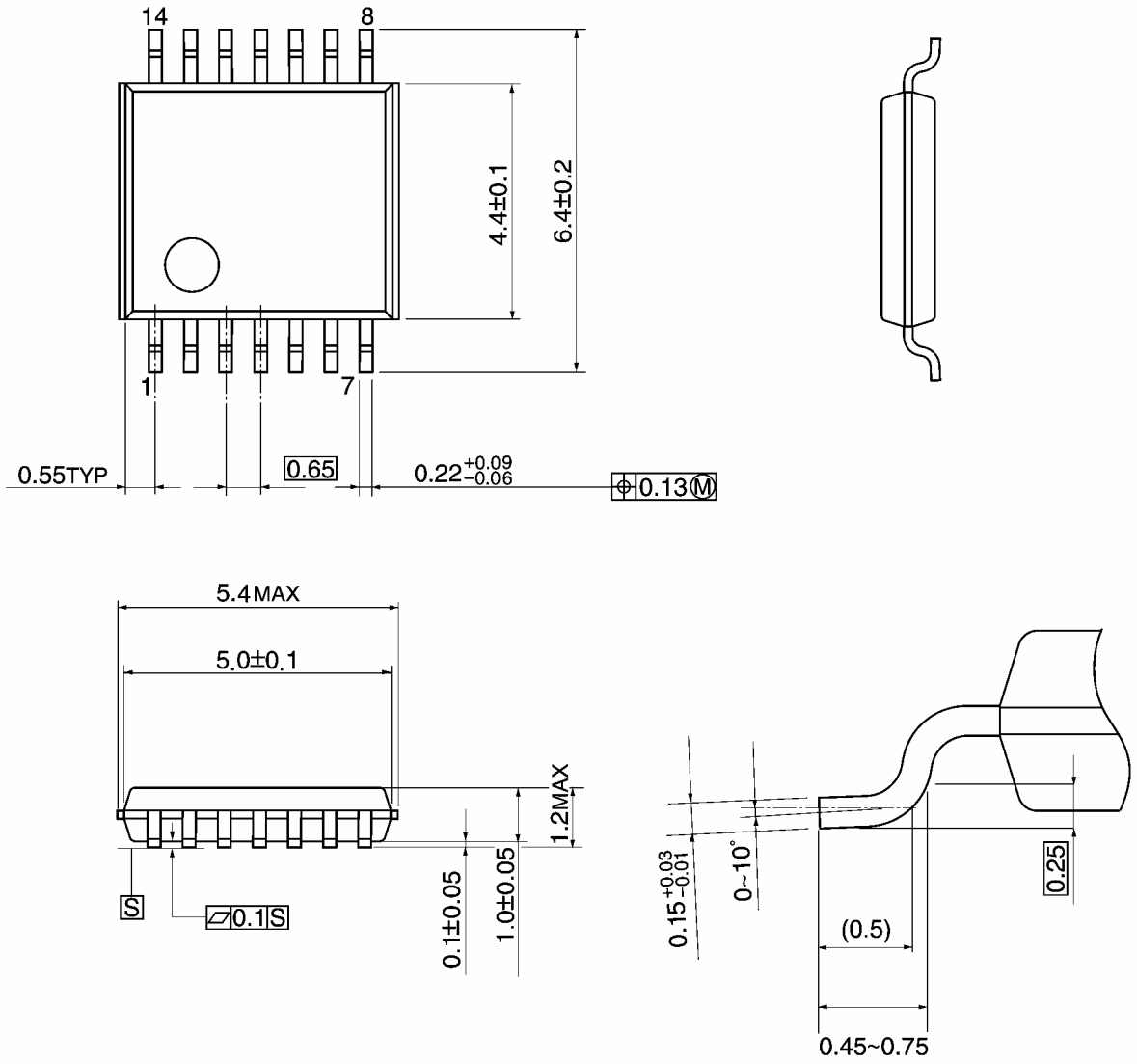


Note: This package is not available in Japan.

Weight: 0.12 g (typ.)

Package Dimensions

TSSOP14-P-0044-0.65A Unit: mm



Weight: 0.06 g (typ.)

Note: Lead (Pb)-Free Packages

DIP14-P-300-2.54 SOP14-P-300-1.27A SOL14-P-150-1.27 TSSOP14-P-0044-0.65A

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20070701-EN

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